



Bipolar NPN Bare Die – BTN6445

Part Description

The BTN6445 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 80V
- VCEO = 65V
- VEBO = 6V
- hFE = 110-450 @ VCE = 5V, IC = 0.002A
- VCE(Sat) = 0.6V @ IC = 0.1A, IB = 5mA
- fT = - MHz @ VCE = - V, IE = -A
- COBO = - pF @ VCB = - V

Features

Low VCE(sat). Designed to provide performance equivalent to BC846

Die Size (Unawn)

330µm X 330µm, 13 Mils X 13 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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